



JCD40SJ65BCT

SiC Schottky Diode

Rev.1.0

DESCRIPTION

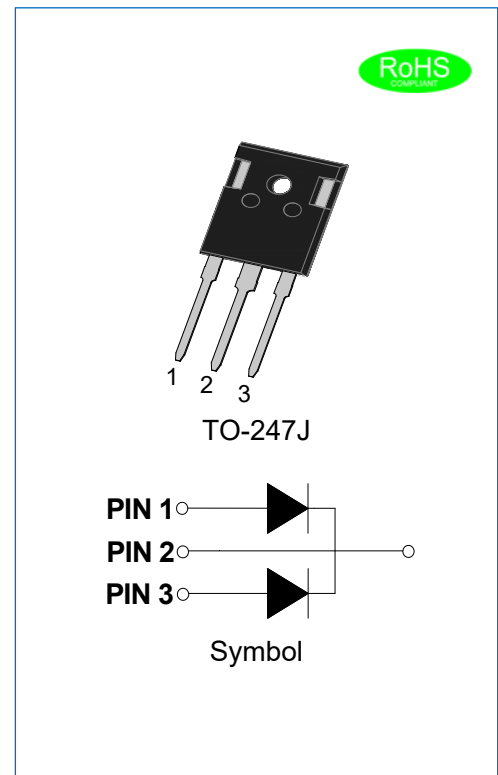
- ✧ 650V Schottky diode
- ✧ Zero reverse recovery current
- ✧ Zero forward recovery voltage
- ✧ High frequency operation
- ✧ Switching characteristics independent of temperature
- ✧ Fast switch
- ✧ Positive temperature coefficient of forward voltage (V_F)

BENEFIT

- ✧ Lower switching loss
- ✧ No thermal runaway in parallel devices
- ✧ Lower heatsink dependent

APPLICATION

- ✧ Switch mode power supplies(SMPS)
- ✧ Boost diodes in PFC or DC/DC stages
- ✧ Free wheeling diodes in inverter stages
- ✧ AC/DC converters



ABSOLUTE MAXIMUM RATING (Rating at 25°C junction temperature unless otherwise specified.)

| Parameter | | Symbol | Value | Unit |
|---|-----------------------------|-------------|-------------|------|
| Maximum repetitive peak reverse voltage | | V_{RRM} | 650 | V |
| Maximum DC blocking voltage | | V_{DC} | 650 | V |
| Average forward current | $T_C=150^{\circ}C$ | $I_{F(AV)}$ | 20* 40** | A |
| Repetitive peak forward surge current | $t_P=10ms, T_C=25^{\circ}C$ | I_{FRM} | 57* | A |
| Non-repetitive peak forward surge current | $t_P=10ms, T_C=25^{\circ}C$ | I_{FSM} | 115* | A |
| Power dissipation | $T_C=25^{\circ}C$ | P_{tot} | 187* | W |
| | $T_C=110^{\circ}C$ | | 81* | |
| Operating junction temperature range | | T_j | -55 to +175 | °C |
| Storage temperature range | | T_{stg} | -55 to +175 | °C |

Note: *per leg, **per device

ELECTRICAL CHARACTERISTICS (Rating at 25°C junction temperature unless otherwise specified.)

| Parameter | Conditions | Symbol | Value | | | Unit |
|---------------------------|-----------------------------|--------|-------|------|------|---------|
| | | | Min. | Typ. | Max. | |
| Forward voltage | $I_F=20A, T_j=25^\circ C$ | V_F | - | 1.35 | 1.62 | V |
| | $I_F=20A, T_j=175^\circ C$ | | - | 1.61 | - | |
| Reverse current | $V_R=650V, T_j=25^\circ C$ | I_R | - | 3 | 80 | μA |
| | $V_R=650V, T_j=175^\circ C$ | | - | 13 | - | |
| Total capacitance | $V_R=1V, f=1MHz$ | C | - | 870 | - | pF |
| | $V_R=200V, f=1MHz$ | | - | 125 | - | |
| | $V_R=400V, f=1MHz$ | | - | 90 | - | |
| Total capacitance charge | $V_R=400V, T_j=25^\circ C$ | Q_C | - | 64 | - | nC |
| Capacitance stored energy | $V_R=400V$ | E_C | - | 9.5 | - | μJ |

THERMAL CHARACTERISTICS

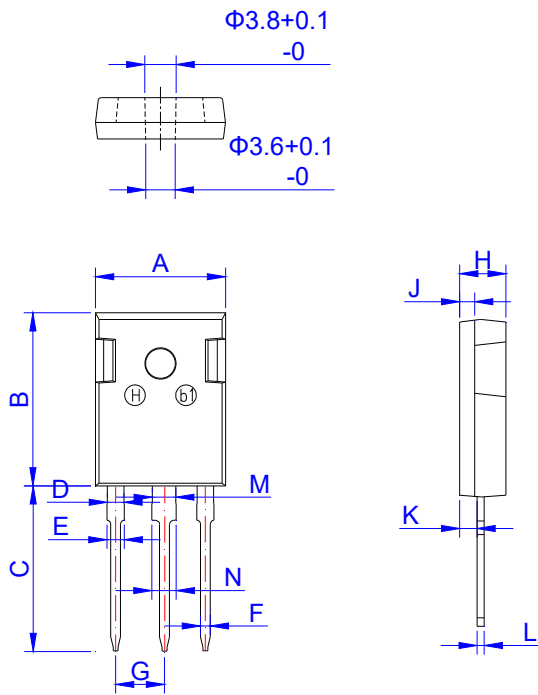
| Symbol | Parameter | Value | Unit |
|---------------|------------------|-------|--------------|
| $R_{th(j-c)}$ | Junction to case | 0.8* | $^\circ C/W$ |

Note: *per leg

ORDERING INFORMATION

| | | | | | | |
|---|--|-------------------------------------|------------------|---|----------------------------------|-----------------------------------|
| <p>J</p> <p>JieJie Microelectronics Co., Ltd</p> <p>SiC Schottky Diode</p> | <p>CD</p> <p>$I_{F(AV)}=40A$</p> | <p>40</p> <p>SJ: TO-247J</p> | <p>SJ</p> | <p>65</p> <p>$V_{RRM}:650V$</p> | <p>B</p> <p>Version B</p> | <p>CT</p> <p>Dual chip</p> |
|---|--|-------------------------------------|------------------|---|----------------------------------|-----------------------------------|

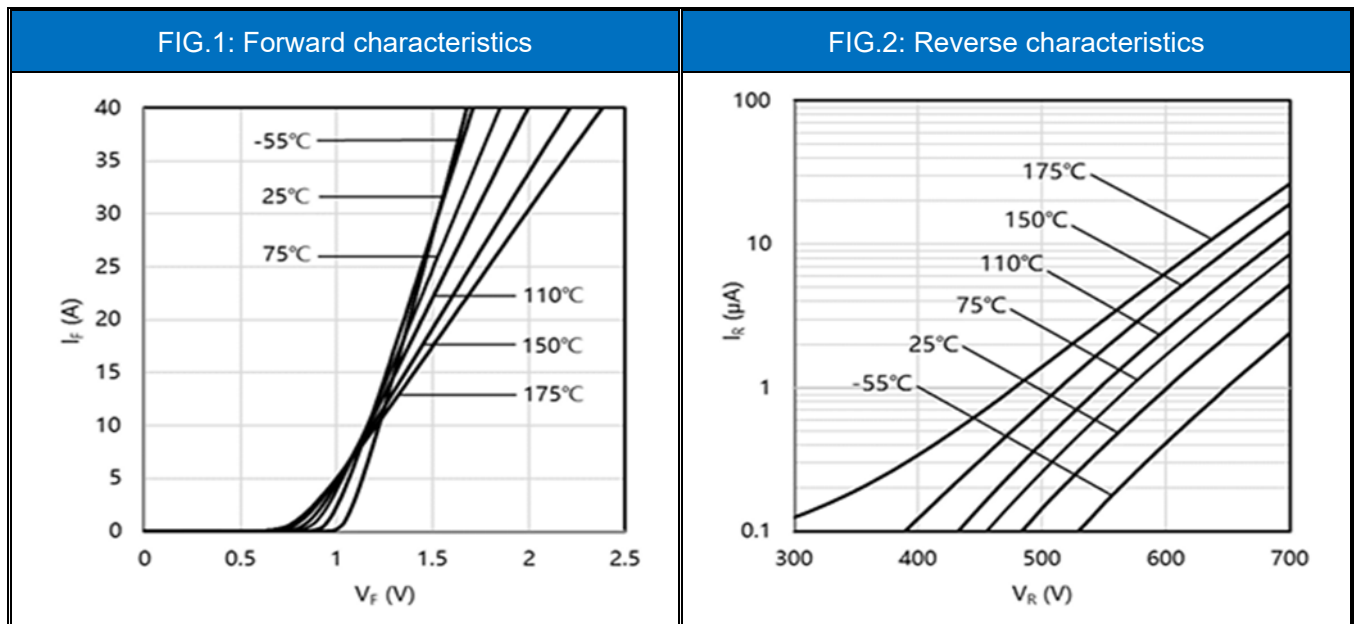
PACKAGE MECHANICAL DATA



| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 15.50 | 15.80 | 16.10 | 0.610 | 0.622 | 0.634 |
| B | 20.80 | 21.00 | 21.20 | 0.819 | 0.827 | 0.835 |
| C | 19.70 | 20.00 | 20.30 | 0.776 | 0.787 | 0.799 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.079 | 0.087 |
| E | 1.90 | 2.10 | 2.30 | 0.075 | 0.083 | 0.091 |
| F | 1.00 | 1.20 | 1.40 | 0.039 | 0.047 | 0.055 |
| G | 5.25 | | 5.65 | 0.207 | | 0.222 |
| H | 4.80 | 5.00 | 5.20 | 0.189 | 0.197 | 0.205 |
| J | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| K | 2.20 | 2.35 | 2.50 | 0.087 | 0.093 | 0.098 |
| L | 0.41 | 0.60 | 0.79 | 0.016 | 0.024 | 0.031 |
| M | 2.80 | 3.00 | 3.20 | 0.110 | 0.118 | 0.126 |
| N | 2.90 | 3.10 | 3.30 | 0.114 | 0.122 | 0.130 |

TO-247J

CHARACTERISTICS CURVE



CHARACTERISTICS CURVE

FIG.3: Capacitance vs. reverse voltage

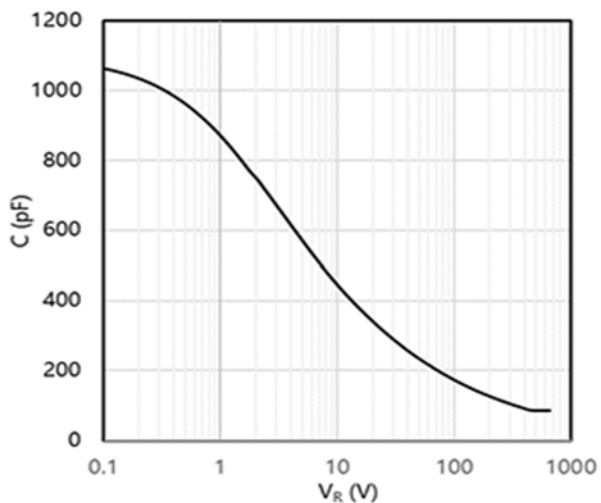


FIG.4: Capacitance charge vs. reverse voltage

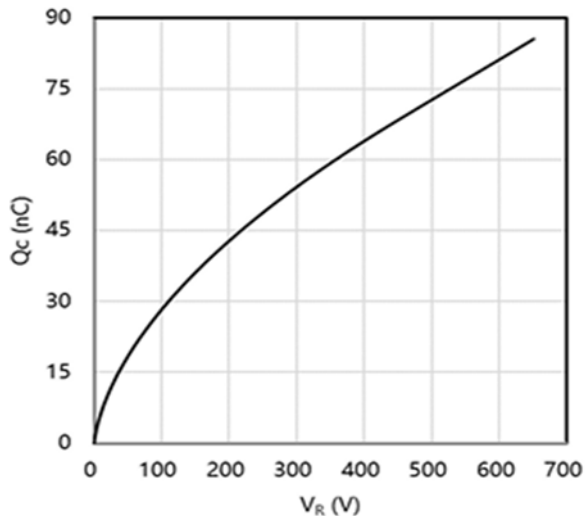


FIG.5: Capacitance stored energy

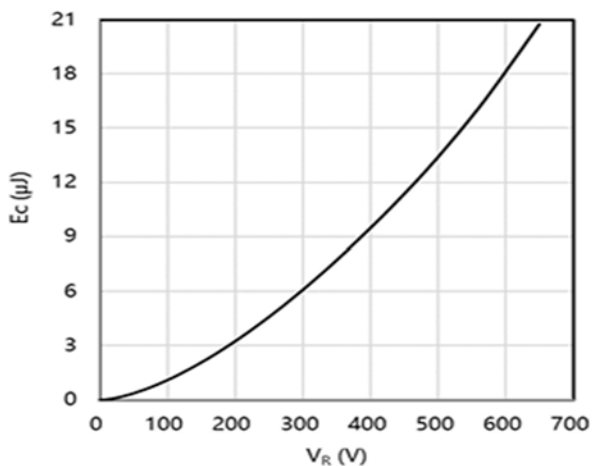


FIG.6: Power derating

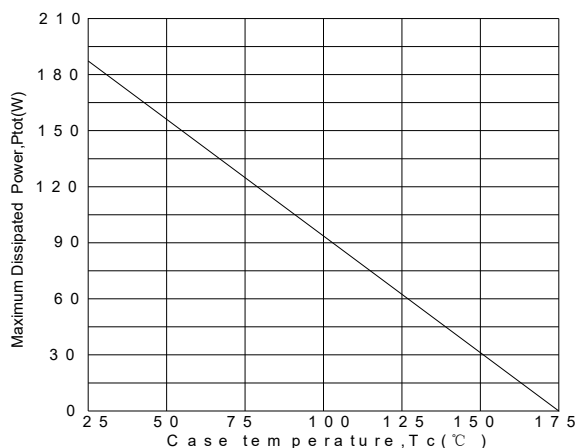


FIG.7: Current derating

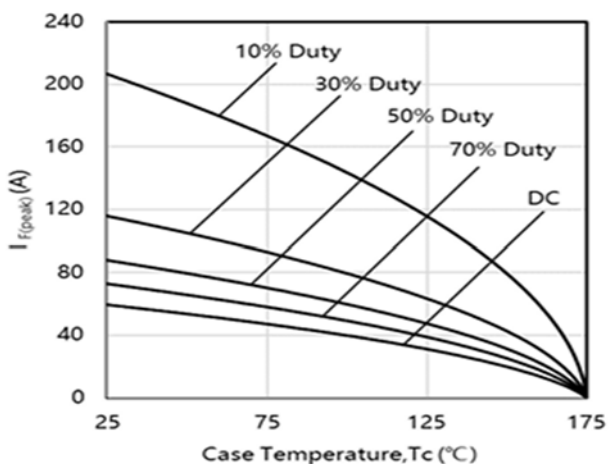
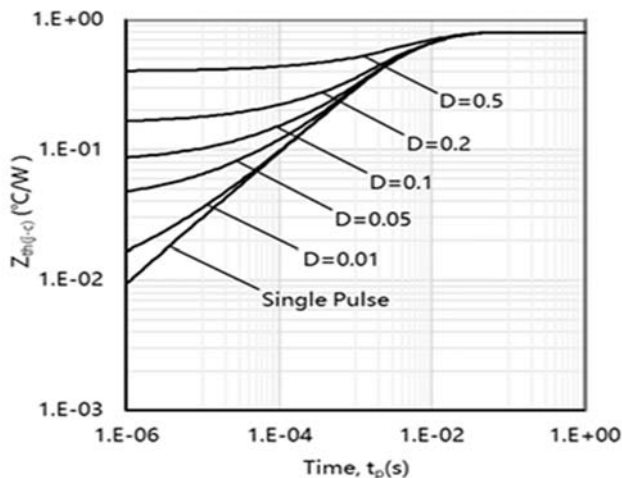


FIG.8: Transient thermal impedance




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